

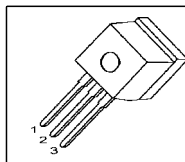
Cool MOS™ Power Transistor

Feature

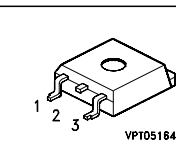
- New revolutionary high voltage technology
- Worldwide best $R_{DS(on)}$ in TO 220
- Ultra low gate charge
- Periodic avalanche rated
- Extreme dv/dt rated
- Ultra low effective capacitances
- Improved noise immunity

V_{DS}	600	V
$R_{DS(on)}$	0.6	Ω
I_D	7.3	A

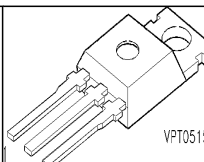
P-TO262



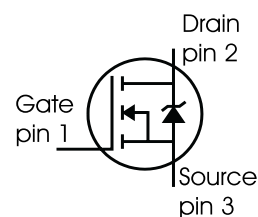
P-TO263-3-2



P-TO220-3-1



Type	Package	Ordering Code	Marking
SPP07N60S5	P-TO220-3-1	Q67040-S4172	07N60S5
SPB07N60S5	P-TO263-3-2	Q67040-S4185	07N60S5
SPI07N60S5	P-TO262	Q67040-S4328	07N60S5



Maximum Ratings, at $T_C = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current $T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	I_D	7.3 4.6	A
Pulsed drain current, t_p limited by T_{jmax}	$I_{D\ puls}$	14.6	
Avalanche energy, single pulse $I_D = -A$, $V_{DD} = 50V$	E_{AS}	230	mJ
Avalanche energy, repetitive t_{AR} limited by $T_{jmax}^{1)}$ $I_D = 7.3A$, $V_{DD} = 50V$	E_{AR}	0.5	
Avalanche current, repetitive t_{AR} limited by T_{jmax}	I_{AR}	7.3	A
Reverse diode dv/dt $I_S = 7.3A$, $V_{DS} < V_{DD}$, $di/dt = 100A/\mu s$, $T_{jmax} = 150^\circ\text{C}$	dv/dt	6	V/ns
Gate source voltage	V_{GS}	± 20	V
Power dissipation, $T_C = 25^\circ\text{C}$	P_{tot}	83	W
Operating and storage temperature	T_j, T_{stg}	-55... +150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - case	R_{thJC}	-	-	1.5	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	62	
SMD version, device on PCB: @ min. footprint @ 6 cm ² cooling area 2)	R_{thJA}	- -	- 35	62 -	
Linear derating factor		-	0.67	-	W/K
Soldering temperature, 1.6 mm (0.063 in.) from case for 10s	T_{sold}	-	-	260	°C

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Static Characteristics

Drain-source breakdown voltage $V_{GS}=0V, I_D=0.25mA$	$V_{(BR)DSS}$	600	-	-	V
Drain-source avalanche breakdown voltage $V_{GS}=0V, I_D=7.3A$	$V_{(BR)DS}$	-	700	-	
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D=350\mu A$	$V_{GS(th)}$	3.5	4.5	5.5	
Zero gate voltage drain current $V_{DS} = 600V, V_{GS} = 0V, T_j = 25\text{ °C}$ $V_{DS} = 600V, V_{GS} = 0V, T_j = 150\text{ °C}$	I_{DSS}	- -	0.5 -	1 100	μA
Gate-source leakage current $V_{GS}=20V, V_{DS}=0V$	I_{GSS}	-	-	100	
Drain-source on-state resistance $V_{GS}=10V, I_D=4.6A, T_j=25\text{ °C}$	$R_{DS(on)}$	-	0.54	0.6	Ω
Gate input resistance $f = 1\text{ MHz, open drain}$	R_G	-	19	-	

¹Repetitive avalanche causes additional power losses that can be calculated as $P_{AV}=E_{AR}*f$.

²Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics , at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Characteristics						
Transconductance	g_{fs}	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$ $I_D = 4.6A$	-	4	-	S
Input capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 25V,$ $f = 1MHz$	-	970	-	pF
Output capacitance	C_{oss}		-	370	-	
Reverse transfer capacitance	C_{rss}		-	10	-	
Effective output capacitance, ¹⁾ energy related	$C_{o(er)}$	$V_{GS} = 0V,$ $V_{DS} = 0V$ to 480V	-	30	-	pF
Effective output capacitance, ²⁾ time related	$C_{o(tr)}$		-	55	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 350V, V_{GS} = 0/10V,$ $I_D = 7.3A, R_G = 12\Omega$	-	120	-	ns
Rise time	t_r		-	40	-	
Turn-off delay time	$t_{d(off)}$		-	170	255	
Fall time	t_f		-	20	30	

Gate Charge Characteristics

Gate to source charge	Q_{gs}	$V_{DD} = 350V$, $I_D = 7.3A$	-	7.5	-	nC
Gate to drain charge	Q_{gd}		-	16.5	-	
Gate charge total	Q_g	$V_{DD} = 350V$, $I_D = 7.3A$, $V_{GS} = 0$ to $10V$	-	27	35	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 350V$, $I_D = 7.3A$	-	8	-	V

¹⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

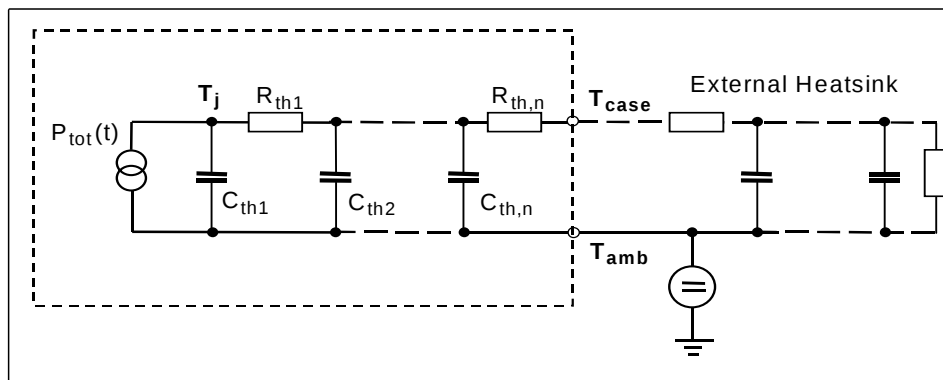
²⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Characteristics						
Inverse diode continuous forward current	I_S	$T_C=25^{\circ}\text{C}$	-	-	7.3	A
Inverse diode direct current, pulsed	I_{SM}		-	-	14.6	
Inverse diode forward voltage	V_{SD}	$V_{GS}=0\text{V}, I_F=I_S$	-	1	1.2	V
Reverse recovery time	t_{rr}	$V_R=350\text{V}, I_F=I_S$, $di_F/dt=100\text{A}/\mu\text{s}$	-	750	1275	ns
Reverse recovery charge	Q_{rr}		-	4.9	-	μC

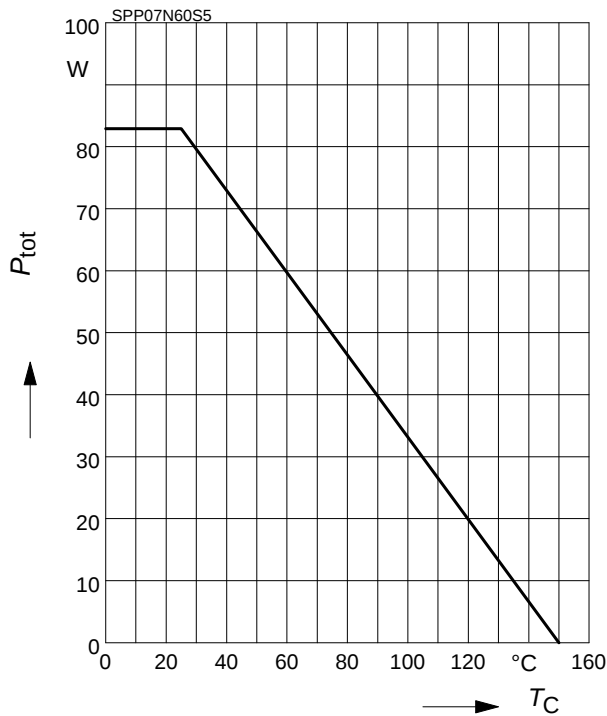
Typical Transient Thermal Characteristics

Symbol	Value	Unit	Symbol	Value	Unit
	typ.			typ.	
Thermal resistance			Thermal capacitance		
R_{th1}	0.024	K/W	C_{th1}	0.0001354	Ws/K
R_{th2}	0.052		C_{th2}	0.0004561	
R_{th3}	0.065		C_{th3}	0.0007717	
R_{th4}	0.172		C_{th4}	0.001013	
R_{th5}	208		C_{th5}	0.00738	
R_{th6}	76		C_{th6}	0.068	



1 Power dissipation

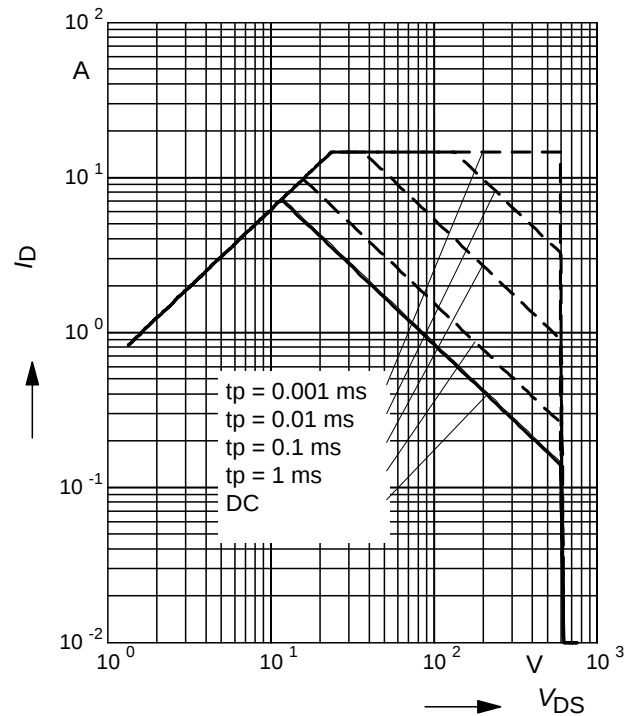
$$P_{\text{tot}} = f(T_C)$$



2 Safe operating area

$$I_D = f(V_{DS})$$

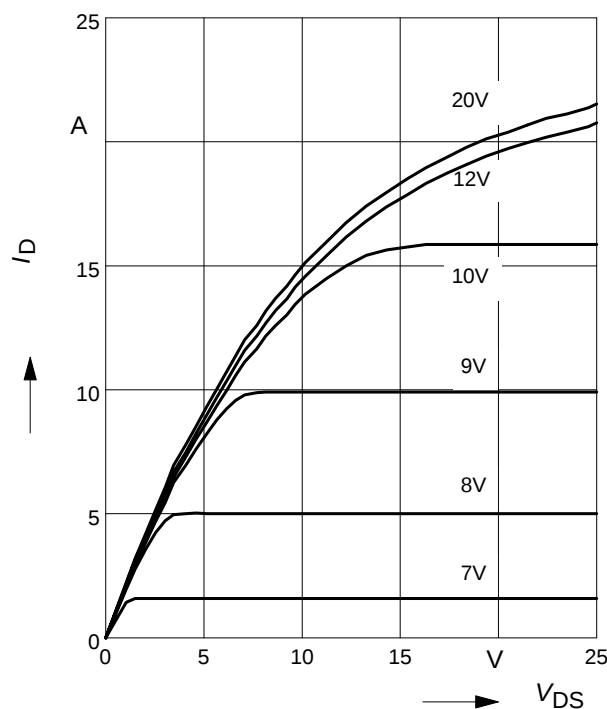
parameter : $D = 0$, $T_C = 25^\circ\text{C}$



3 Typ. output characteristic

$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$$

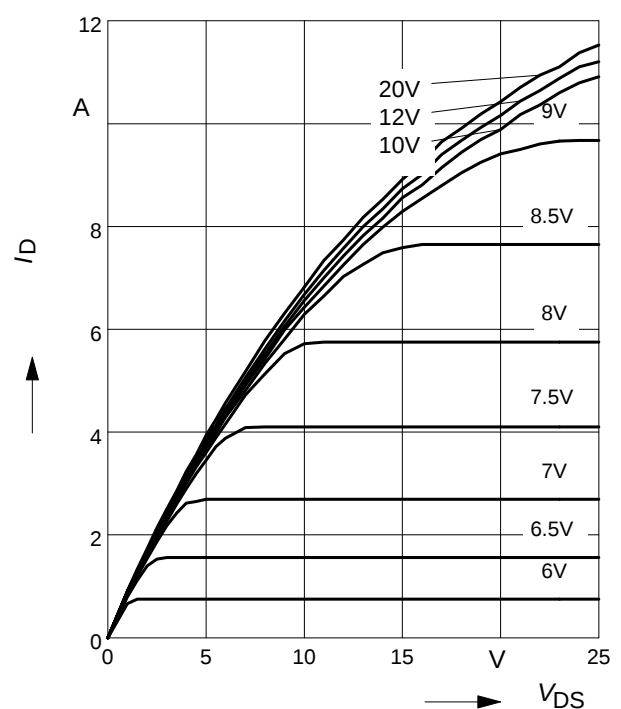
parameter: $t_p = 10 \mu\text{s}$, V_{GS}



4 Typ. output characteristic

$$I_D = f(V_{DS}); T_j = 150^\circ\text{C}$$

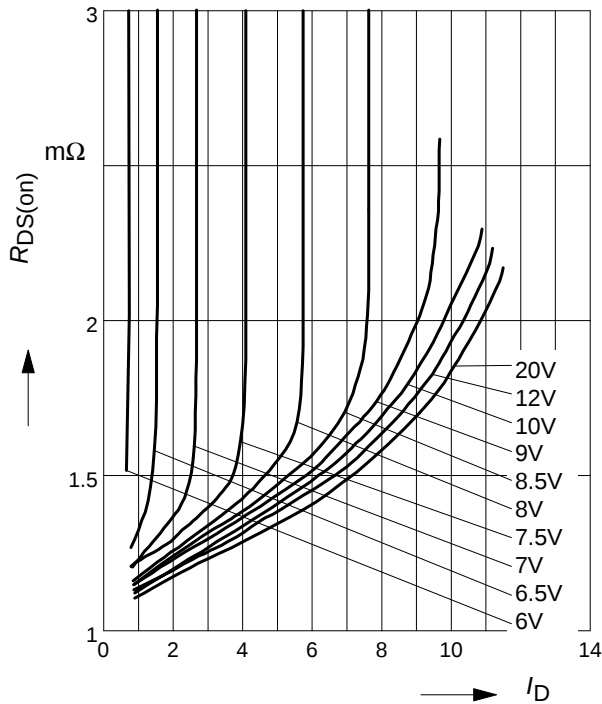
parameter: $t_p = 10 \mu\text{s}$, V_{GS}



5 Typ. drain-source on resistance

$$R_{DS(on)} = f(I_D)$$

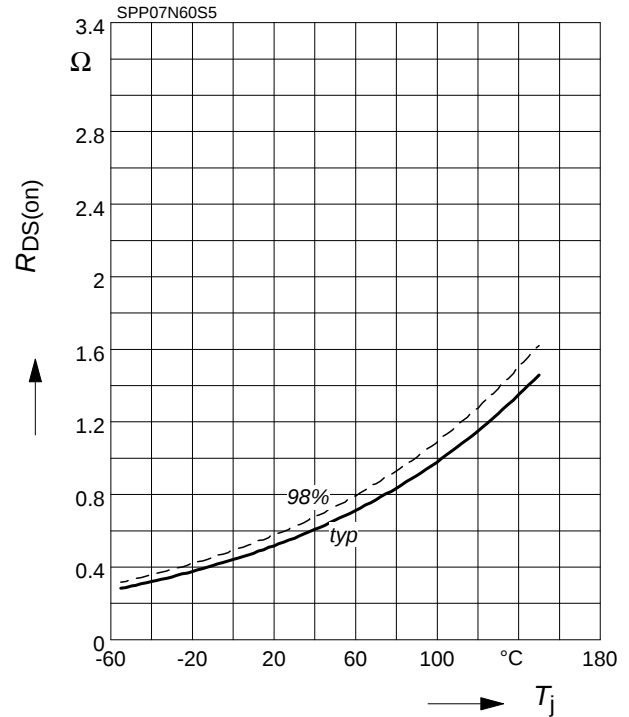
parameter: $T_j = 150^\circ\text{C}$, V_{GS}



6 Drain-source on-state resistance

$$R_{DS(on)} = f(T_j)$$

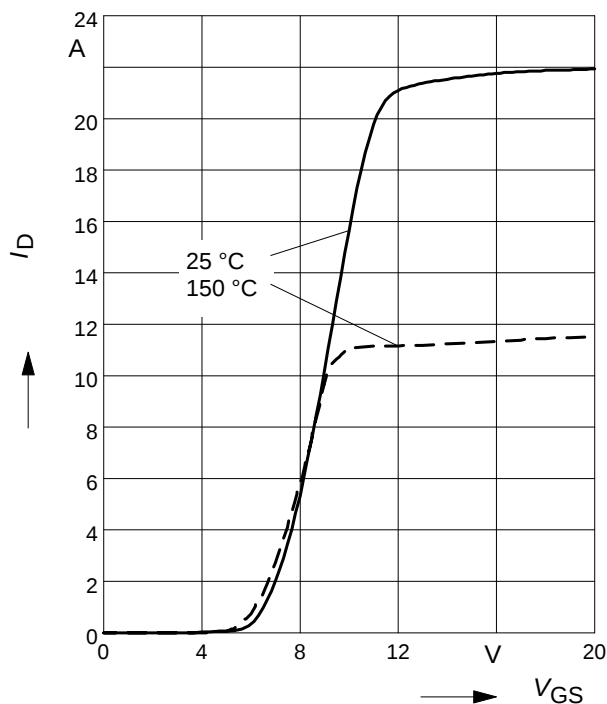
parameter: $I_D = 4.6\text{ A}$, $V_{GS} = 10\text{ V}$



7 Typ. transfer characteristics

$$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$

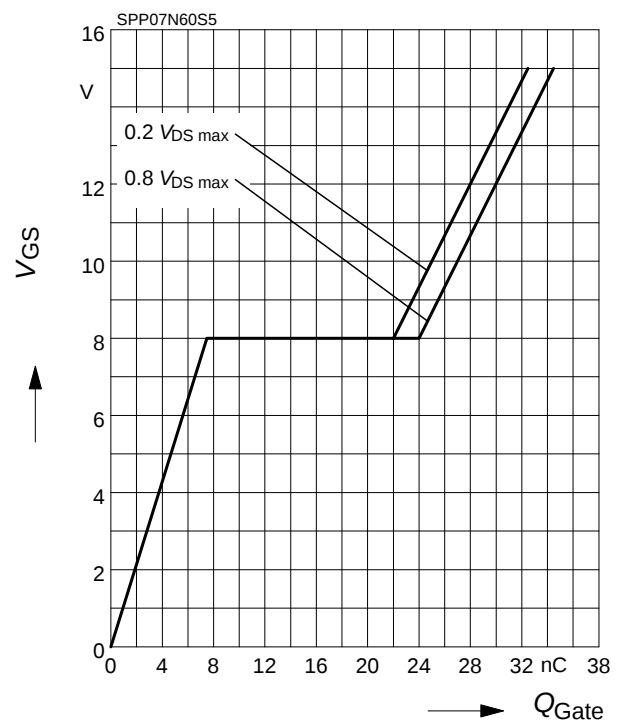
parameter: $t_p = 10\text{ }\mu\text{s}$



8 Typ. gate charge

$$V_{GS} = f(Q_{Gate})$$

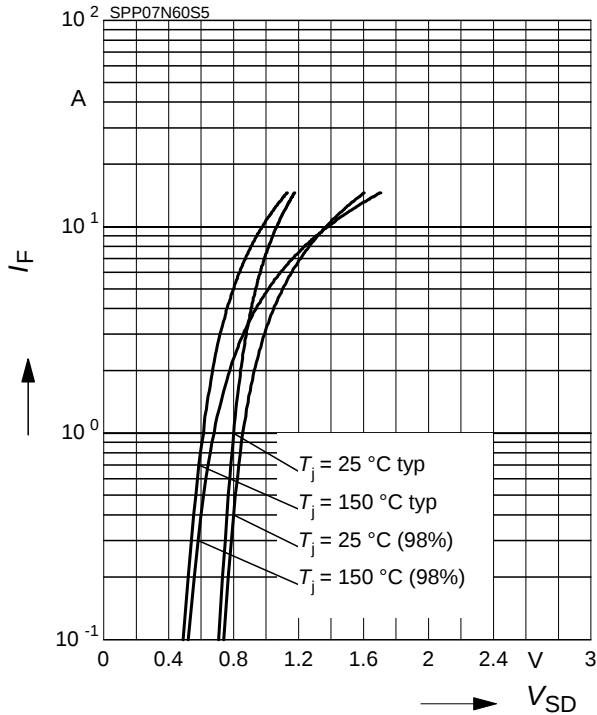
parameter: $I_D = 7.3\text{ A}$ pulsed



9 Forward characteristics of body diode

$$I_F = f(V_{SD})$$

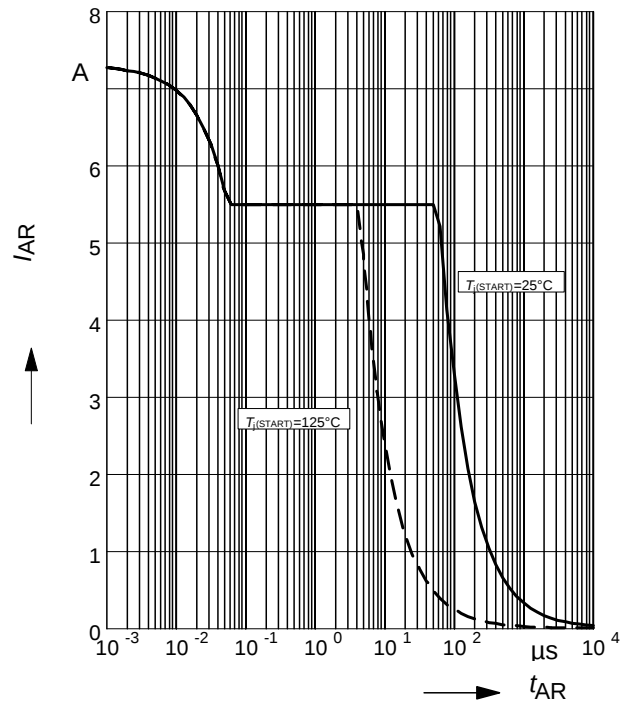
parameter: T_j , $t_p = 10 \mu s$



10 Avalanche SOA

$$I_{AR} = f(t_{AR})$$

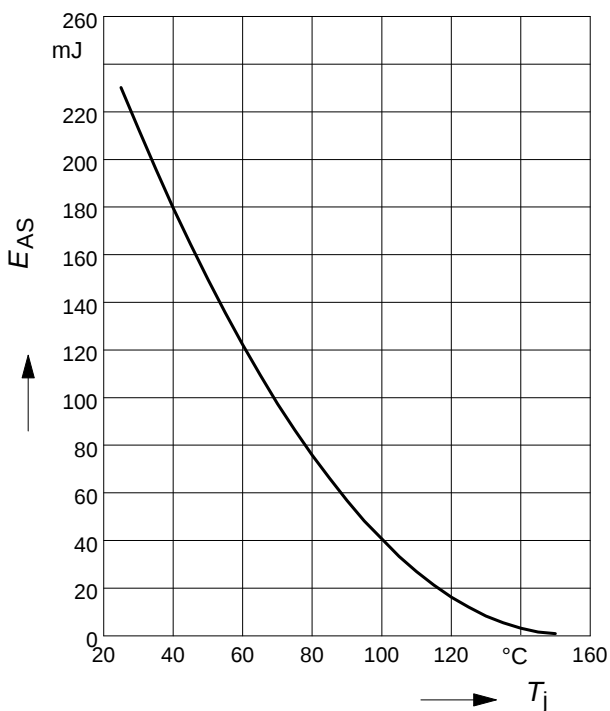
par.: $T_j \leq 150 \text{ } ^\circ\text{C}$



11 Avalanche energy

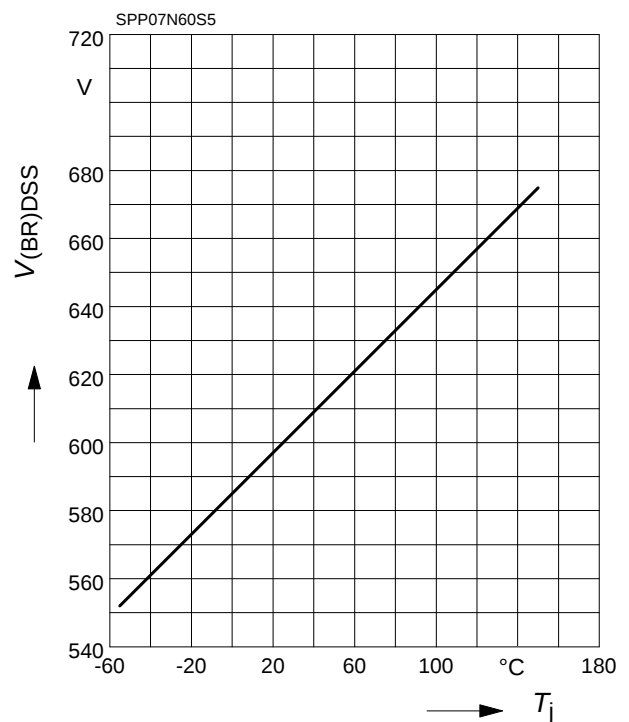
$$E_{AS} = f(T_j)$$

par.: $I_D = -A$, $V_{DD} = 50 \text{ V}$



12 Drain-source breakdown voltage

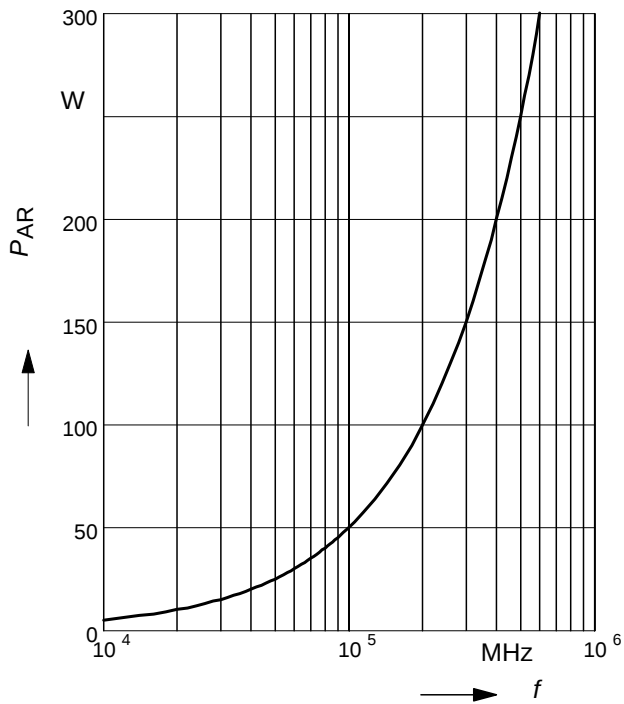
$$V_{(BR)DSS} = f(T_j)$$



13 Avalanche power losses

$$P_{AR} = f(f)$$

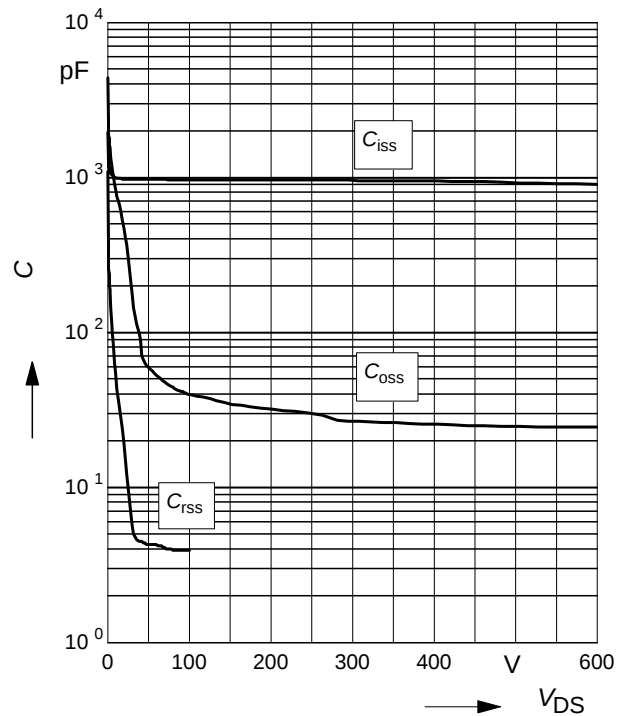
parameter: $E_{AR}=0.5\text{mJ}$



14 Typ. capacitances

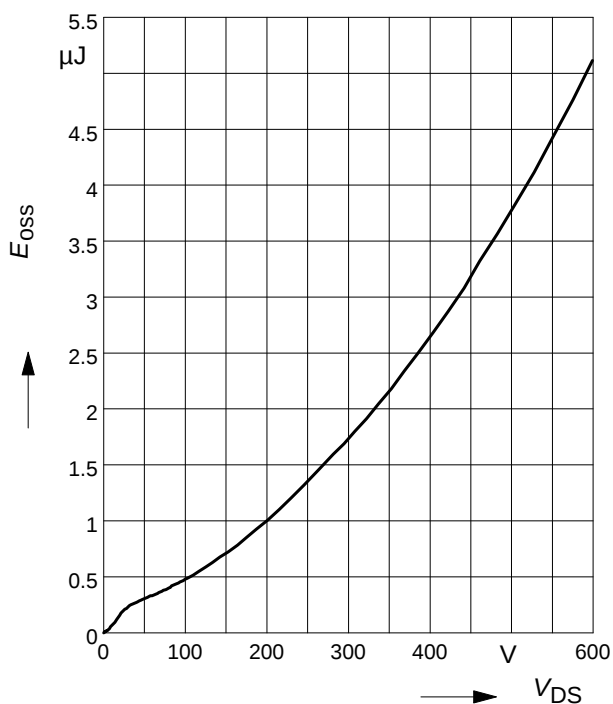
$$C = f(V_{DS})$$

parameter: $V_{GS}=0\text{V}$, $f=1\text{ MHz}$

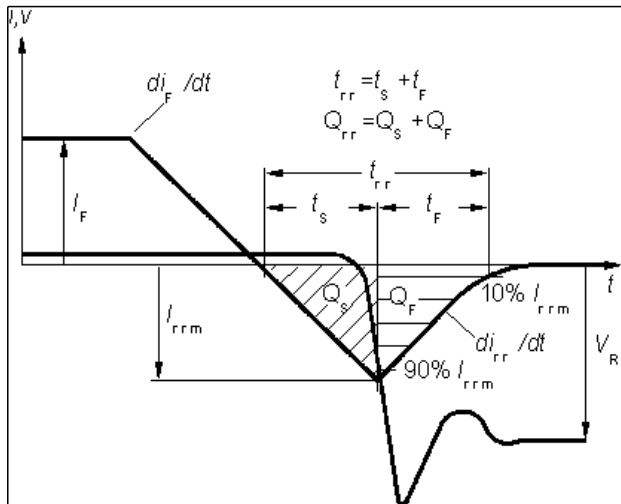


15 Typ. C_{oss} stored energy

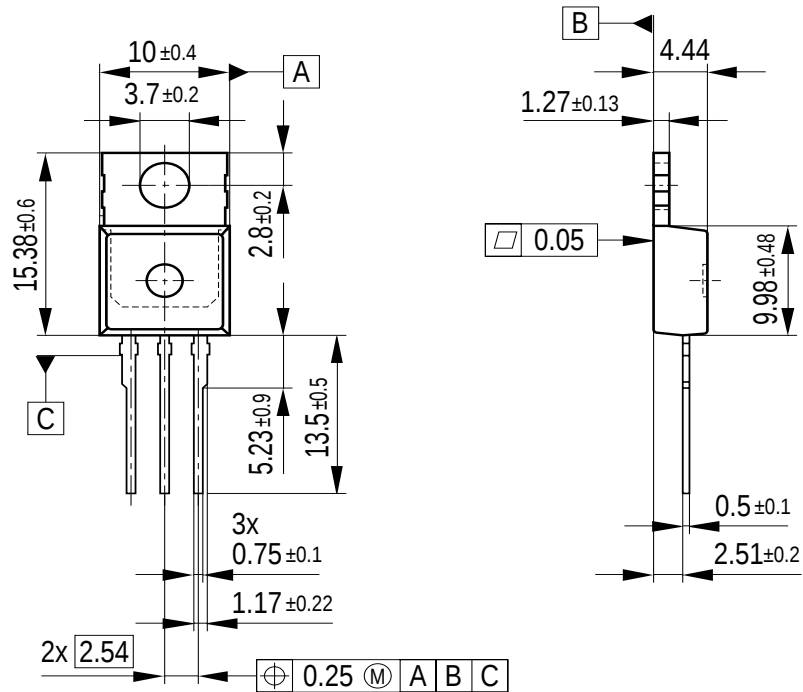
$$E_{oss}=f(V_{DS})$$



Definition of diodes switching characteristics

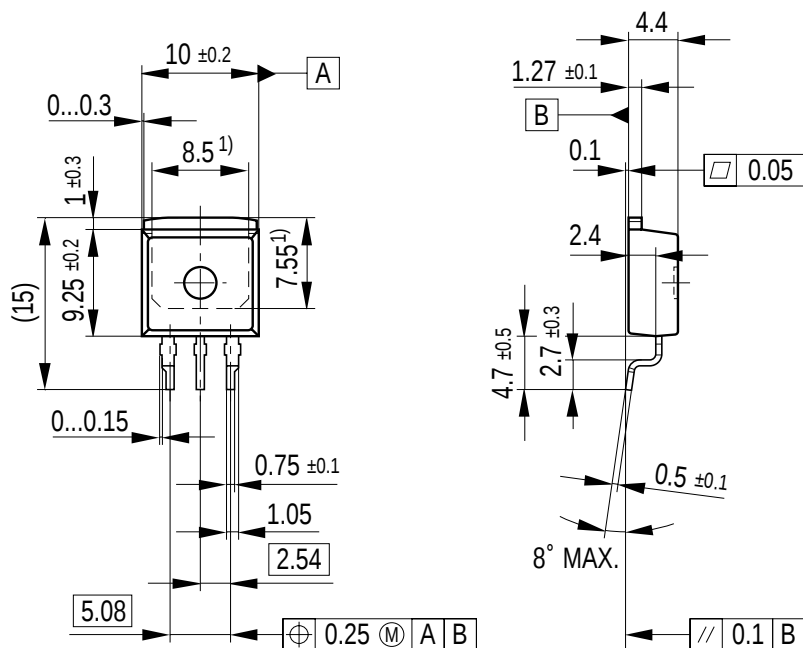


P-TO-220-3-1



All metal surfaces tin plated, except area of cut.
Metal surface min. x=7.25, y=12.3

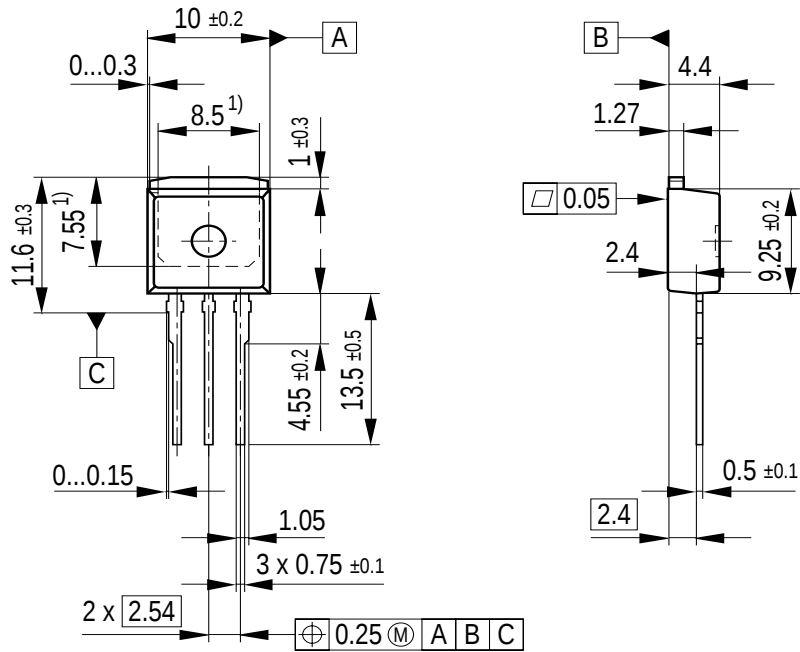
P-TO-263-3-1 (D²-PAK)



¹⁾ Typical

All metal surfaces: tin plated, except area of cut.
Metal surface min. x=7.25, y=6.9

P-TO-262-3-1 (I²-PAK)



¹⁾ Typical

Metal surface min. X = 7.25, Y = 6.9

All metal surfaces tin plated, except area of cut.

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